Yunqiu Wu

List of Publications by Citations

95 papers	714 citations	14 h-index	21 g-index
124 ext. papers	1,001 ext. citations	2.5 avg, IF	4.18 L-index

#	Paper	IF	Citations
95	. *IEEE Journal of Solid-State Circuits*, **2017**, 52, 2892-2904	5.5	56
94	A Scalable Large-Signal Multiharmonic Model of AlGaN/GaN HEMTs and Its Application in C-Band High Power Amplifier MMIC. *IEEE Transactions on Microwave Theory and Techniques*, **2017**, 65, 2836-2846	4.1	48
93	Analysis and Design of Ultra-Wideband mm-Wave Injection-Locked Frequency Dividers Using Transformer-Based High-Order Resonators. *IEEE Journal of Solid-State Circuits*, **2018**, 53, 2177-2189	5.5	37
92	Analysis and Equivalent-Circuit Model for CMOS On-Chip Multiple Coupled Inductors in the Millimeter-Wave Region. *IEEE Transactions on Electron Devices*, **2015**, 62, 3957-3964	2.9	29
91	Triple band-notched UWB monopole antenna on ultra-thin liquid crystal polymer based on ESCSRR. *Electronics Letters*, **2017**, 53, 57-58	1.1	26
90	Temperature-Dependent Access Resistances in Large-Signal Modeling of Millimeter-Wave AlGaN/GaN HEMTs. *IEEE Transactions on Microwave Theory and Techniques*, **2017**, 65, 2271-2278	4.1	25
89	Analysis and Design of Inductorless Wideband Low-Noise Amplifier With Noise Cancellation Technique. *IEEE Access*, **2017**, 5, 9389-9397	3.5	24
88	A Broadband and Equivalent-Circuit Model for Millimeter-Wave On-Chip M:N Six-Port Transformers and Baluns. *IEEE Transactions on Microwave Theory and Techniques*, **2015**, 63, 3109-3121	4.1	22
87	An Injection-Current-Boosting Locking-Range Enhancement Technique for Ultra-Wideband mm-Wave Injection-Locked Frequency Triplers. *IEEE Transactions on Microwave Theory and Techniques*, **2019**, 67, 3174-3186	4.1	21
86	**2019**,		17
85	A 62-90 GHz High Linearity and Low Noise CMOS Mixer Using Transformer-Coupling Cascode Topology. *IEEE Access*, **2018**, 6, 19338-19344	3.5	17
84	A CMOS K-Band 6-bit Attenuator With Low Phase Imbalance for Phased Array Applications. *IEEE Access*, **2017**, 5, 19657-19661	3.5	17
83	A 256-QAM 39 GHz Dual-Channel Transceiver Chipset with LTCC Package for 5G Communication in 65 nm CMOS **2018**,		16
82	Microwave transmission properties of chemical vapor deposition graphene. *Applied Physics Letters*, **2012**, 101, 053110	3.4	16
81	An On-Chip Frequency-Reconfigurable Antenna For Q-Band Broadband Applications. *IEEE Antennas and Wireless Propagation Letters*, **2017**, 16, 2232-2235	3.8	14
80	A Ku band 4-Element phased array transceiver in 180 nm CMOS **2017**,		13
79	High-Temperature-Annealed Flexible Carbon Nanotube Network Transistors for High-Frequency Wearable Wireless Electronics. *ACS Applied Materials & Interfaces*, **2020**, 12, 26145-26152	9.5	12

78	An Improved Ultrawideband Open-Short De-Embedding Method Applied up to 220 GHz. *IEEE Transactions on Components, Packaging and Manufacturing Technology*, **2018**, 8, 269-276	1.7	11
77	A Compact Ka-Band Active Integrated Antenna With a GaAs Amplifier in a Ceramic Package. *IEEE Antennas and Wireless Propagation Letters*, **2017**, 16, 2416-2419	3.8	11
76	An Ultralow Phase Noise Eight-Core Fundamental 62-to-67-GHz VCO in 65-nm CMOS. *IEEE Microwave and Wireless Components Letters*, **2019**, 29, 125-127	2.6	11
75	A Hybrid Integrated High-Gain Antenna With an On-Chip Radiator Backed by Off-Chip Ground for System-on-Chip Applications. *IEEE Transactions on Components, Packaging and Manufacturing Technology*, **2017**, 7, 114-122	1.7	10
74	X-band flexible bandpass filter based on ultra-thin liquid crystal polymer substrate. *Electronics Letters*, **2015**, 51, 345-347	1.1	10
73	Analytical Gate Capacitance Models for Large-Signal Compact Model of AlGaN/GaN HEMTs. *IEEE Transactions on Electron Devices*, **2019**, 66, 357-363	2.9	10
72	A 39 GHz MIMO Transceiver Based on Dynamic Multi-Beam Architecture for 5G Communication with 150 Meter Coverage **2018**,		10
71	A 220-GHz Compact Equivalent Circuit Model of CMOS Transistors. *IEEE Microwave and Wireless Components Letters*, **2017**, 27, 651-653	2.6	9
70	An Improved RF MOSFET Model Accounting Substrate Coupling Among Terminals. *IEEE Microwave and Wireless Components Letters*, **2018**, 28, 138-140	2.6	9
69	A 60-GHz Variable Gain Phase Shifter With 14.8-dB Gain Tuning Range and 6-Bit Phase Resolution Across −25 °C–110 °C. *IEEE Transactions on Microwave Theory and Techniques*, **2021**, 69, 2371-2385	4.1	8
68	Characterization of CVD graphene permittivity and conductivity in micro-/millimeter wave frequency range. *AIP Advances*, **2016**, 6, 095014	1.5	8
67	A Large-Signal Statistical Model and Yield Estimation of GaN HEMTs Based on Response Surface Methodology. *IEEE Microwave and Wireless Components Letters*, **2016**, 26, 690-692	2.6	8
66	A 19.5% Efficiency 51–73-GHz High-Output Power Frequency Doubler in 65-nm CMOS. *IEEE Microwave and Wireless Components Letters*, **2019**, 29, 818-821	2.6	8
65	A Wideband Model for On-Chip Interconnects With Different Shielding Structures. *IEEE Transactions on Components, Packaging and Manufacturing Technology*, **2017**, 7, 1702-1712	1.7	7
64	A 21.7-to-41.7-GHz Injection-Locked LO Generation With a Narrowband Low-Frequency Input for Multiband 5G Communications. *IEEE Transactions on Microwave Theory and Techniques*, **2020**, 68, 170-183	4.1	7
63	A 37–40-GHz Low-Phase-Imbalance CMOS Attenuator With Tail-Capacitor Compensation Technique. *IEEE Transactions on Circuits and Systems I: Regular Papers*, **2020**, 67, 3400-3409	3.9	6
62	. *IEEE Access*, **2020**, 8, 29311-29318	3.5	6
61	Compact multi-band transversal bandpass filters with source–load coupling. *Journal of Electromagnetic Waves and Applications*, **2014**, 28, 184-193	1.3	6

60	Support Vector Regression for Measuring Electromagnetic Parameters of Magnetic Thin-Film Materials. *IEEE Transactions on Magnetics*, **2007**, 43, 4071-4075	2	6
59	A 21-to-41-GHz High-Gain Low Noise Amplifier With Triple-Coupled Technique for Multiband Wireless Applications. *IEEE Transactions on Circuits and Systems II: Express Briefs*, **2021**, 68, 1857-1861	3.5	6
58	Flexible Graphene Field-Effect Transistors With Extrinsic ${f}_{{{mathrm{max}}}}$ of 28 GHz. *IEEE Electron Device Letters*, **2018**, 39, 1944-1947	4.4	6
57	An Equivalent Circuit Model With Current Return Path Effects for ON-Chip Interconnect up to 80 GHz. *IEEE Transactions on Components, Packaging and Manufacturing Technology*, **2015**, 5, 1320-1330	1.7	5
56	A K-Band Frequency Tripler Using Transformer-Based Self-Mixing Topology With Peaking Inductor. *IEEE Transactions on Microwave Theory and Techniques*, **2020**, 68, 1688-1696	4.1	5
55	A Ku-Band 8-Element Phased-Array Transmitter with Built-in-Self-Test Capability **2018**,		5
54	An improved small-signal equivalent circuit model for 4H-SIC power mesfets. *Microwave and Optical Technology Letters*, **2008**, 50, 1455-1458	1.2	5
53	An Improved Large Signal Model for 0.1 μm AlGaN/GaN High Electron Mobility Transistors (HEMTs) Process and Its Applications in Practical Monolithic Microwave Integrated Circuit (MMIC) Design in W band. *Micromachines*, **2018**, 9,	3.3	5
52	A 51.5 - 64.5 GHz Active Phase Shifter Using Linear Phase Control Technique With 1.4° Phase resolution in 65-nm CMOS **2019**,		4
51	A 62–85-GHz High Linearity Upconversion Mixer With 18-GHz IF Bandwidth. *IEEE Microwave and Wireless Components Letters*, **2019**, 29, 219-221	2.6	4
50	A 22.4-to-40.6-GHz Multi-Ratio Injection-Locked Frequency Multiplier with 57.7-dBc Harmonic Rejection **2020**,		4
49	An Improved Small-Signal Equivalent Circuit Model Considering Channel Current Magnetic Effect. *IEEE Microwave and Wireless Components Letters*, **2018**, 28, 804-806	2.6	4
48	Multimode orbital angular momentum antenna based on four-arm planar spiral. *Electronics Letters*, **2019**, 55, 875-876	1.1	4
47	A novel dual-band bandpass filter using CRLH triangle mushroom structure and DGS. *Microwave and Optical Technology Letters*, **2013**, 55, 2756-2759	1.2	4
46	A 27.5–43.5 GHz high linearity up-conversion CMOS mixer for 5G communication **2017**,		4
45	**2017**,		4
44	CMOS 90 nm multi-bias transistor model Up to 66 GHz **2017**,		4
43	Flexible microwave filters on ultra thin Liquid Crystal Polymer substrate **2015**,		4

42	A novel tri-band band-pass filter using combined simplified CRLH and right-handed SIRs. *Journal of Electromagnetic Waves and Applications*, **2013**, 27, 999-1007	1.3	4
41	A 5-Gb/s 66 dB CMOS Variable-Gain Amplifier With Reconfigurable DC-Offset Cancellation for Multi-Standard Applications. *IEEE Access*, **2018**, 6, 54139-54146	3.5	4
40	A Ku-band Phased Array in Package Integrating Four 180 nm CMOS Transceivers with On-chip Antennas **2018**,		4
39	A 27.9–33.5-GHz transformer-based injection-locked frequency divider with 62.9% locking range **2017**,		3
38	An Improved Surface Potential-Based High-Order Channel Length Modulation Model **2019**,		3
37	Multi-bias Small Signal Circuit Model for FinFET Transistors **2019**,		3
36	RF CMOS Transistor Equivalent Circuit Model up to 66 GHz **2018**,		3
35	. *IEEE Transactions on Microwave Theory and Techniques*, **2021**, 69, 3989-4000	4.1	3
34	A Quasi-Physical Large-Signal Statistical Model for 0.15 μm AlGaN/GaN HEMTs Process **2019**,		2
33	A 24 GHz CMOS mixer using symmetrical design methodology with I/Q imbalance calibration **2017**,		2
32	A Bendable Microwave GaN HEMT on CVD Parylene-C Substrate **2020**,		2
31	A Ka-Band CMOS Variable Gain Amplifier with High Gain Resolution and Low Phase Variation **2020**,		2
30	A 68.5~90 GHz High-Gain Power Amplifier With Capacitive Stability Enhancement Technique in 0.13 μm SiGe BiCMOS. *IEEE Transactions on Microwave Theory and Techniques*, **2020**, 1-1	4.1	2
29	A 15-27 GHz Low Conversion Loss and High Isolation Resistive Ring Mixer for Direct Conversion Receiver **2019**,		2
28	A 10-mW 3.9-dB NF transformer-based V-band low-noise amplifier in 65-nm CMOS. *International Journal of Numerical Modelling: Electronic Networks, Devices and Fields*, **2020**, 33, e2576	1	2
27	An improved open-short equivalent circuit model for CMOS transistors de-embedding. *International Journal of Numerical Modelling: Electronic Networks, Devices and Fields*, **2020**, 33, e2589	1	2
26	An improved wideband equivalent circuit model for integrated spiral inductors in CMOS technology. *International Journal of Numerical Modelling: Electronic Networks, Devices and Fields*, **2020**, 33, e2640	1	2
25	A Wideband CMOS Frequency Quadrupler With Transformer-Based Tail Feedback Loop. *IEEE Transactions on Circuits and Systems II: Express Briefs*, **2021**, 68, 1153-1157	3.5	2

24	A 2.9 GHz CMOS Phase-Locked Loop with Improved Ring Oscillator **2019**,		1
23	A Scalable Model of On-Chip Inductor Including Tunable Dummy Metal Density Factor. *IEEE Transactions on Components, Packaging and Manufacturing Technology*, **2019**, 9, 296-305	1.7	1
22	An Improved Surface-Potential-Based Model for MOSFETs Considering the Carrier Gaussian Distribution. *IEEE Transactions on Microwave Theory and Techniques*, **2020**, 68, 4082-4090	4.1	1
21	An asynchronous dual switch envelope tracking supply modulator with 86% efficiency. *IEICE Electronics Express*, **2018**, 15, 20180206-20180206	0.5	1
20	66 GHz bias-dependent equivalent circuit model for CMOS transistor based on 90 nanometers CMOS technology. *Microwave and Optical Technology Letters*, **2018**, 60, 1808-1812	1.2	1
19	A 33–41-GHz SiGe-BiCMOS Digital Step Attenuator With Minimized Unit Impedance Variation. *IEEE Transactions on Very Large Scale Integration (VLSI) Systems*, **2021**, 29, 568-579	2.6	1
18	A SiGe Power Amplifier With Double Gain Peaks Based on the Control of Stationary Points of Impedance Transformation. *IEEE Transactions on Microwave Theory and Techniques*, **2021**, 69, 2279-2290	4.1	1
17	An Improved Large-Signal Equivalent Circuit Model for Partially Depleted Silicon-on-Insulator MOSFET. *IEEE Transactions on Microwave Theory and Techniques*, **2021**, 69, 2972-2980	4.1	1
16	Complete model for CMOS transistors up to 66GHz **2016**,		1
15	An Improved Small Signal Equivalent Circuit Modeling Based On 65nm CMOS Technology **2019**,		1
14	Differential low-loss T/R switch for phase array application in 0.18-μm CMOS technology. *IET Microwaves, Antennas and Propagation*, **2019**, 13, 813-818	1.6	1
13	A High Linearity Low Noise Amplifier for 5G Front-End Modules **2019**,		1
12	Millimeter wave balun design and optimization based on compensation matching capacitors and active S parameter. *International Journal of Numerical Modelling: Electronic Networks, Devices and Fields*, **2020**, 33, e2644	1	1
11	A millimeter-wave scalable small signal model of RF CMOS transistor against number of fingers. *International Journal of Numerical Modelling: Electronic Networks, Devices and Fields*, **2020**, 33, e2608	1	1
10	A package-level wideband driver amplifier with 134% fractional bandwidth. *IEICE Electronics Express* , **2018**, 15, 20180179-20180179	0.5	1
9	An Empirical Nonlinear Capacitance Model for SOI Transistor **2018**,		1
8	A Ka-Band CMOS Phase-Invariant and Ultralow Gain Error Variable Gain Amplifier With Active Cross-Coupling Neutralization and Asymmetric Capacitor Techniques. *IEEE Transactions on Microwave Theory and Techniques*, **2022**, 70, 85-100	4.1	0
7	A Harmonic-Tuned VCO With an Intrinsic-High-Q F23 Inductor in 65-nm CMOS. *IEEE Microwave and Wireless Components Letters*, **2020**, 30, 981-984	2.6	0

List of Publications

6	A microwave amplifier behavioral model capable of cascade simulation. *Microwave and Optical Technology Letters*, **2021**, 63, 2113-2121	1.2	0
5	A new multipassband filter with multiple transmission zeros based on quarter-wavelength resonators in wireless communication systems. *Microwave and Optical Technology Letters*, **2015**, 57, 1105-1107	1.2	
4	A 27.5-43.5 GHz 65-nm CMOS up-conversion mixer with 0.42 dBm OP1dB for 5G applications. *International Journal of Numerical Modelling: Electronic Networks, Devices and Fields*, **2020**, 33, e2550	1	
3	A 3-GHz Inverse-Coupled Current-Reuse VCO Implemented by 1:1 Transformer. *IEEE Microwave and Wireless Components Letters*, **2022**, 1-3	2.6	
2	A Ku-Band Eight-Element Phased-Array Transmitter With Built-in Self-Test Capability in 180-nm CMOS Technology. *IEEE Transactions on Very Large Scale Integration (VLSI) Systems*, **2022**, 1-12	2.6	
1	Temperature-Dependent Threshold Voltage Extraction of FinFETs Using Noise Measurements. *IEEE Transactions on Microwave Theory and Techniques*, **2022**, 1-1	4.1	